## NSN 5962-01-356-9153

Memory Microcircuit - Page 1 of 1



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| Operating Tempurature Range:                       |
|--|
| -55.0/+125.0 degrees celsius                       |
| Storage Tempurature Range:                         |
| -65.0/+150.0 degrees celsius                       |
| End Application:                                   |
| Milstar  |
| Features Provided:                                 |
| Electrostatic sensitive and radiation hardened     |
| Inclosure Material:                                |
| Ceramic  |
| Inclosure Configuration:                           |
| Flat pack  |
| Output Logic Form:                                 |
| Complementary-metal oxide-semiconductor logic      |
| Criticality Code Justification:                    |
| Cbbl and feat and nhcf                             |
| Case Outline Source And Designator:                |
| Mil-m-38510  |
| Product Name:                                      |
| Microcircuit, digital-cmos dual port, sram, 2k x 8 |
| Voltage Rating And Type Per Characteristic:        |
| -0.5 volts total supply and 7.0 volts total supply |
| Memory Device Type:                                |
| Ram  |
| Special Features:                                  |
| Rad hard per raytheon g371916 andansi y14.5m-1982  |
| Nuclear Hardness Critical Feature:                 |
| Hardened   |
| Terminal Type And Quantity:                        |
| 48 flat leads                                      |
| Shelf Life:  |
| N/a  |
| Unit Of Measure:                                   |
| <del>-</del>                                       |
| Demilitarization:                                  |
| Yes - demil/mli                                    |
| Fiig:  |
| A458a0   |
| Mil-std (military Standard):                       |
| Mil m 29510 anno                                   |

Mil-m-38510 spec.